

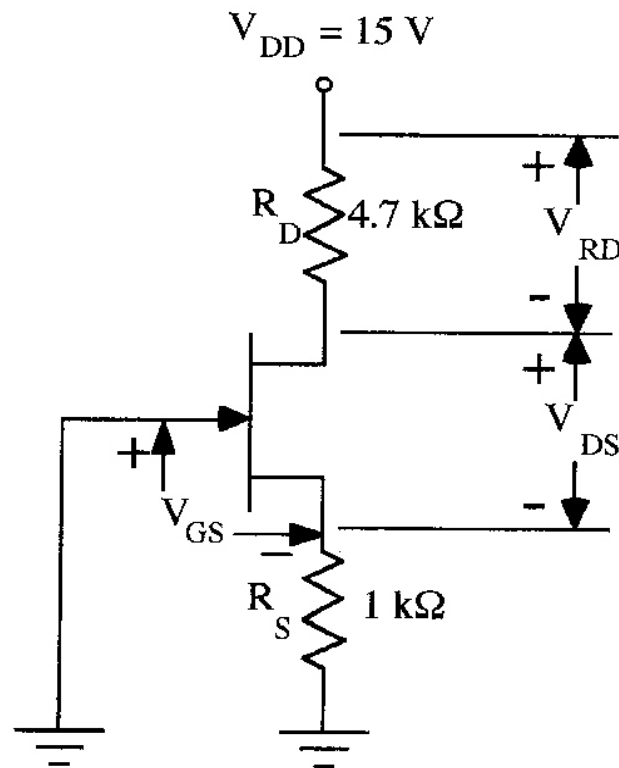
# Lab 7

JFET Biasing  
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## Objective

- Investigate the JFET self-bias configuration.
- Investigate the JFET voltage-divider bias configuration.
- Calculate JFET dc q-points for each bias configuration

## Results



**Figure 3**

$I_{DSS}$  and  $V_p$  for the JFET must be calculated based on the actual transistor itself. In doing this, I determined the values to be as follows:

$$I_{DSS} = 6.79\text{ mA}$$

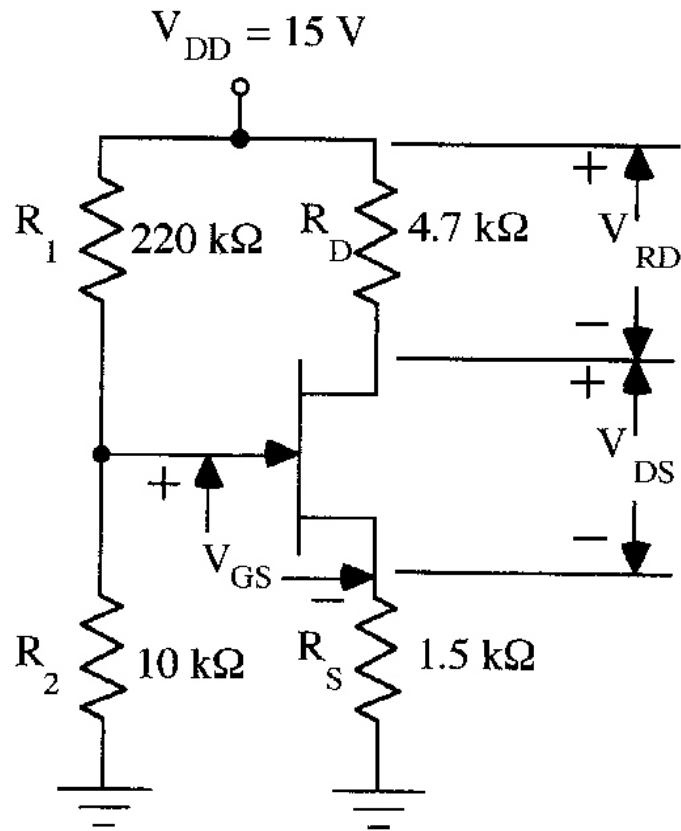
$$V_p = 2.906\text{ V}$$

$$V_{rd} = 7.27\text{ V}$$

$$V_{ds} = 6.18\text{ V}$$

$$V_{gs} = 1.55\text{ V}$$

Given  $V_{gs}$ , I was able to calculate  $I_d = I_{DSS}(1 - V_{gs}/V_p)^2 = 1.48\text{ mA}$



**Figure 4**

$$V_{gs} = 1.57\text{ V}$$

$$V_{ds} = 5.85\text{ V}$$

$$V_{rd} = 6.92\text{ V}$$

$$I_d = I_{dss}(1 - V_{gs}/V_p)^2 = 1.44\text{ mA}$$

### Analysis

In a self-biased JFET circuit,  $I_d = I_{dss}$  when  $V_g = 0\text{ V}$ .

In a voltage-divider JFET circuit, the load line crosses  $I_d = 0$  when  $V_{gs} > 0\text{ V}$ , therefore  $I_d = I_{dss}$  occurs